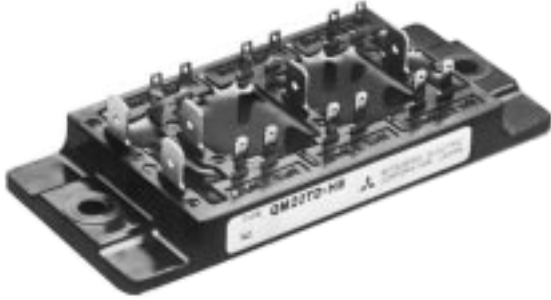


# QM20TD-HB

MEDIUM POWER SWITCHING USE  
INSULATED TYPE

**QM20TD-HB**



- **IC** Collector current ..... **20A**
- **V<sub>CEX</sub>** Collector-emitter voltage ..... **600V**
- **h<sub>FE</sub>** DC current gain ..... **250**
- **Insulated Type**
- **UL Recognized**

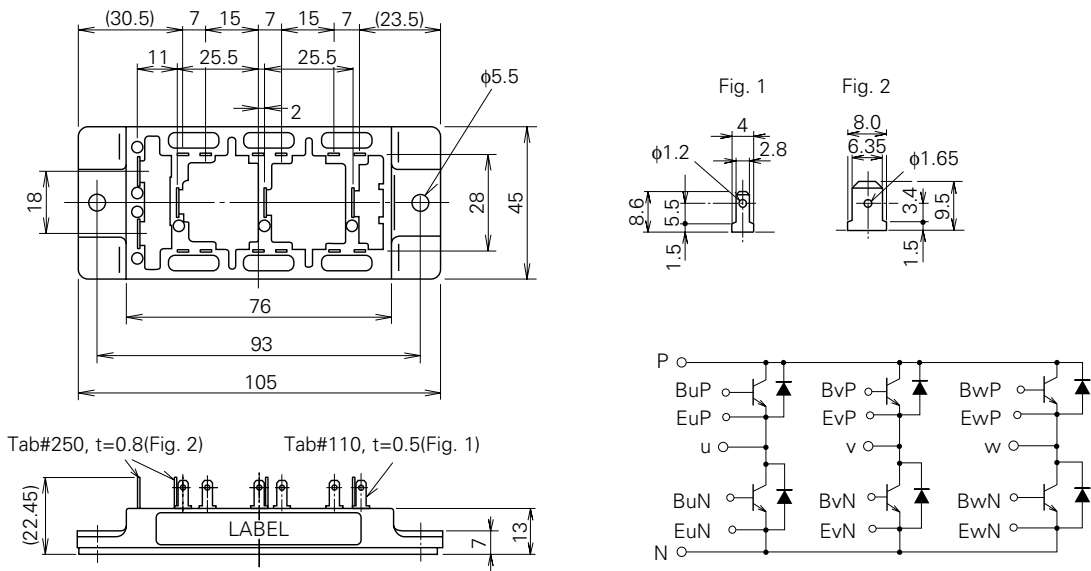
Yellow Card No. E80276 (N)  
File No. E80271

**APPLICATION**

Inverters, Servo drives, DC motor controllers, NC equipment, Welders

**OUTLINE DRAWING & CIRCUIT DIAGRAM**

Dimensions in mm



Note: All Transistor Units are Darlingtons.

**QM20TD-HB**

**MEDIUM POWER SWITCHING USE  
INSULATED TYPE**

**ABSOLUTE MAXIMUM RATINGS** (T<sub>j</sub>=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Ratings	Unit
V <sub>CEX</sub> (SUS)	Collector-emitter voltage	I <sub>C</sub> =1A, V <sub>EB</sub> =2V	600	V
V <sub>CEX</sub>	Collector-emitter voltage	V <sub>EB</sub> =2V	600	V
V <sub>CBO</sub>	Collector-base voltage	Emitter open	600	V
V <sub>EBO</sub>	Emitter-base voltage	Collector open	7	V
I <sub>C</sub>	Collector current	DC	20	A
-I <sub>C</sub>	Collector reverse current	DC (forward diode current)	20	A
P <sub>C</sub>	Collector dissipation	T <sub>C</sub> =25°C	83	W
I <sub>B</sub>	Base current	DC	1	A
-I <sub>CSM</sub>	Surge collector reverse current (forward diode current)	Peak value of one cycle of 60Hz (half wave)	200	A
T <sub>j</sub>	Junction temperature		-40~+150	°C
T <sub>stg</sub>	Storage temperature		-40~+125	°C
V <sub>iso</sub>	Isolation voltage	Charged part to case, AC for 1 minute	2500	V
—	Mounting torque	Mounting screw M5	1.47~1.96	N·m
—	Weight	Typical value	15~20	kg·cm
—	Weight	Typical value	90	g

**ELECTRICAL CHARACTERISTICS** (T<sub>j</sub>=25°C, unless otherwise noted)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
I <sub>C</sub> EX	Collector cutoff current	V <sub>CE</sub> =600V, V <sub>EB</sub> =2V	—	—	1.0	mA
I <sub>C</sub> BO	Collector cutoff current	V <sub>CB</sub> =600V, Emitter open	—	—	1.0	mA
I <sub>E</sub> BO	Emitter cutoff current	V <sub>EB</sub> =7V	—	—	40	mA
V <sub>CE</sub> (sat)	Collector-emitter saturation voltage	I <sub>C</sub> =20A, I <sub>B</sub> =80mA	—	—	2.0	V
V <sub>BE</sub> (sat)	Base-emitter saturation voltage		—	—	2.5	V
-V <sub>CEO</sub>	Collector-emitter reverse voltage	-I <sub>C</sub> =20A (diode forward voltage)	—	—	1.5	V
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =20A, V <sub>CE</sub> =2V	250	—	—	—
t <sub>on</sub>	Switching time	V <sub>CC</sub> =300V, I <sub>C</sub> =20A, I <sub>B1</sub> =120mA, I <sub>B2</sub> =-400mA	—	—	1.5	μs
t <sub>s</sub>			—	—	12	μs
t <sub>f</sub>			—	—	2.0	μs
R <sub>th</sub> (j-c) Q	Thermal resistance (junction to case)	Transistor part (per 1/6 module)	—	—	1.5	°C/W
R <sub>th</sub> (j-c) R		Diode part (per 1/6 module)	—	—	2.5	°C/W
R <sub>th</sub> (c-f)	Contact thermal resistance (case to fin)	Conductive grease applied (per 1/6 module)	—	—	0.35	°C/W